



PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

Pan et al.

Serial No.: 09/614,113

Filed: July 12, 2000

For: METHODS OF FORMING A GATE
STACK THAT IS VOID OF SILICON
CLUSTERS WITHIN A METALLIC
SILICIDE FILM THEREOF (as amended)

Confirmation No.: 1710

Examiner: D. Deo

Group Art Unit: 1765

Attorney Docket No.: 2269-2915.3US
(96-0149.02/US)

Notice of Allowance Mailed:

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AMENDMENT PURSUANT TO 37 C.F.R. § 1.312(a)

Mail Stop ISSUE FEE
Commissioner for Patents
P.O. Box 1450
Alexandria, Virginia 22313-1450

Sir:

Please amend the above-referenced application as follows:

Amendments to the Title appear on page 3 of this paper.

Match and Return

Amendments to the Specification appear on page 4 of this paper.

Amendments to the Claims are reflected in the listing of claims which begins on page 5 of this paper.

Amendments to the Drawings appear on page 8 of this paper and include both an attached replacement sheet and an annotated sheet showing changes.

Remarks begin on page 9 of this paper.

An **Appendix** including amended drawing figures is attached following page 9 of this paper.

IN THE TITLE:

The title has been amended herein. Pursuant to 37 C.F.R. §§ 1.121 and 1.125 (as amended to date), please enter the title as amended.

**TECHNIQUE FOR ELIMINATION OF PITTING ON
SILICON SUBSTRATE DURING GATE STACK ETCH
METHODS OF FORMING A GATE STACK THAT IS VOID OF
SILICON CLUSTERS WITHIN A METALLIC SILICIDE FILM THEREOF**